

(54) Title of the invention : CIRCUIT AND A METHOD FOR OPERATING QUASI FLOATING BULK DIRECT GATE DRIVEN MOSFET

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(57) Abstract :
 A circuit to operate a metal oxide semiconductor field effect transistor. The circuit includes a first sub-circuit including a first DC bias voltage source, a second DC bias voltage source, a first MOS device, a second MOS device, a third MOS device, a first capacitor and a second capacitor. The circuit also includes a second sub-circuit including a third DC bias voltage source, a fourth DC bias voltage source, a fourth MOS device, a fifth MOS device, a sixth MOS device, a third capacitor and a fourth capacitor. The circuit further includes a third sub circuit including a seventh primary MOS device, a seventh secondary MOS device, an eighth primary MOS device, an eighth secondary MOS device, a ninth first-primary MOS device, a ninth second-primary MOS device, a ninth first-secondary MOS device, a ninth second-secondary MOS device, a tenth primary MOS device and a tenth secondary MOS device.

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